

1 **ABSTRACT OF THE DISCLOSURE**

2 A method of forming an isolation trench in a semiconductor
3 includes forming a first isolation trench portion having a first depth and
4 having a first sidewall intersecting a surface of the semiconductor at a
5 first angle. The method also includes forming a second isolation trench
6 portion within and extending below the first isolation trench portion. The
7 second isolation trench portion has a second depth and includes a second
8 sidewall. The second sidewall intersects the first sidewall at an angle
9 with respect to the surface that is greater than the first angle. A
10 dielectric material fills the first and second isolation trench portions.

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